

# SKNH 132/18 E H4



SEMIPACK® 2

## Thyristor / Diode Modules

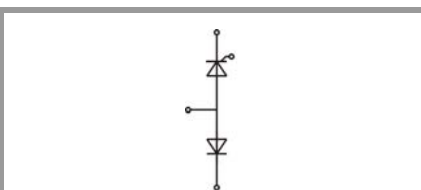
### SKNH 132/18 E H4

#### Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E63532

#### Typical Applications\*

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)
- DC braking of AC motors

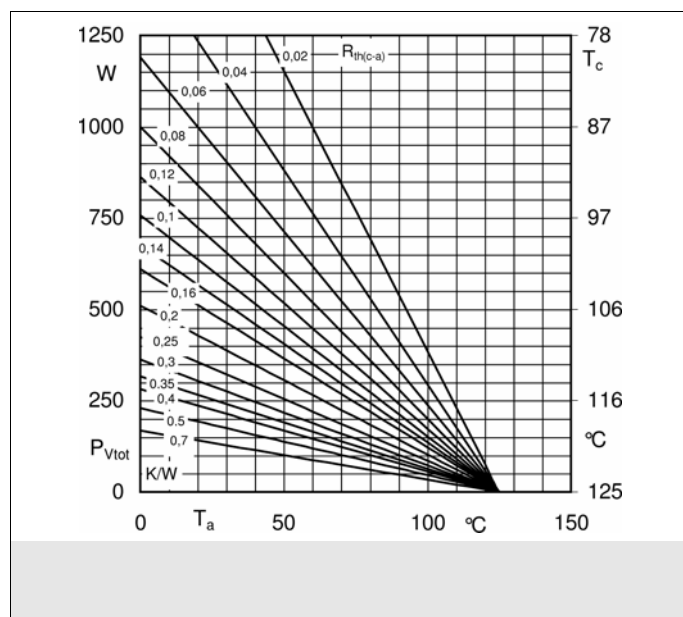
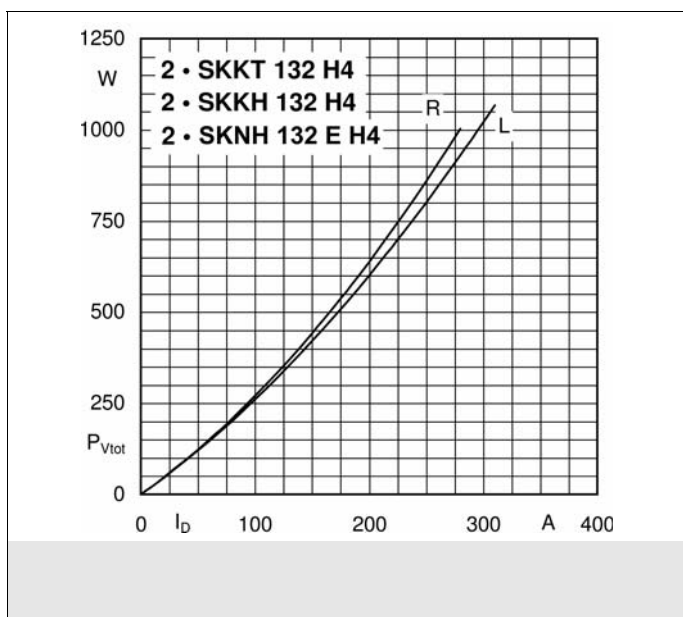
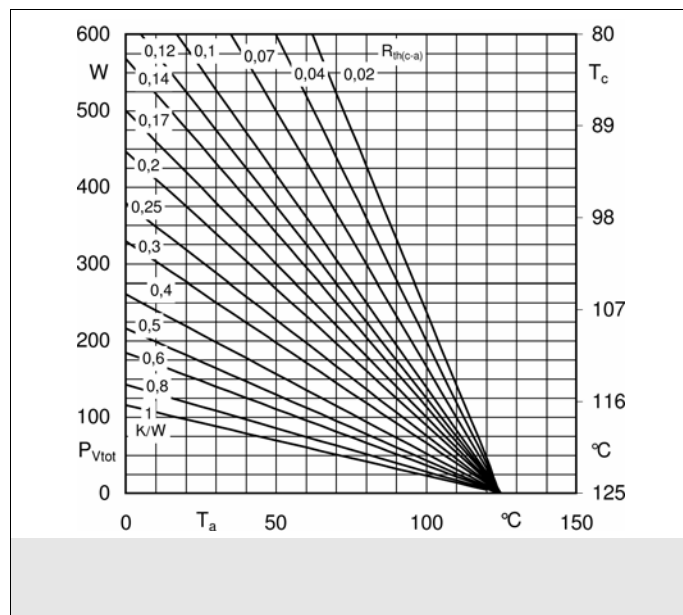
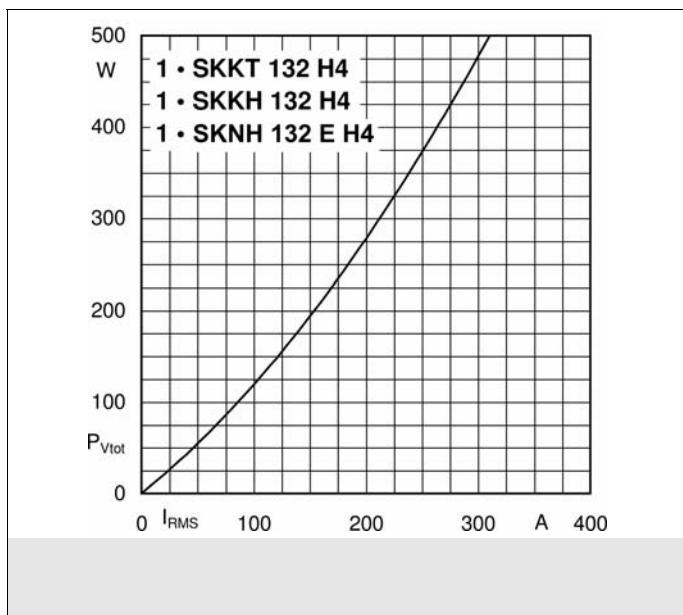
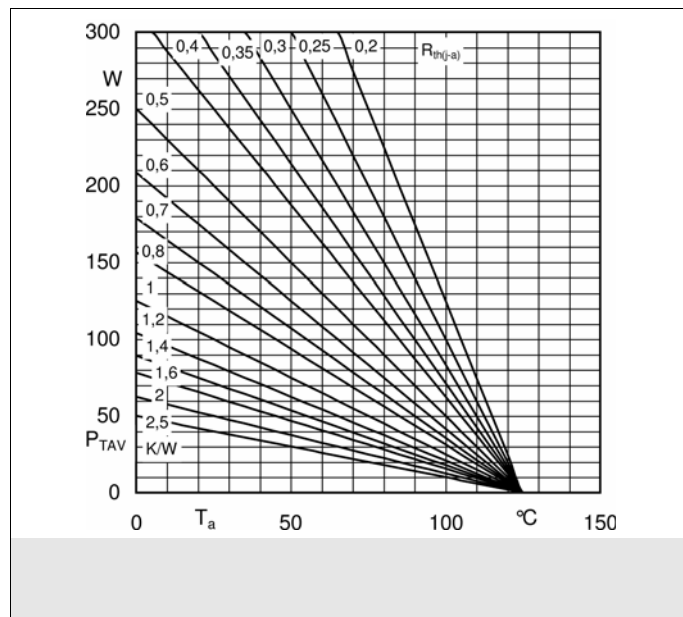
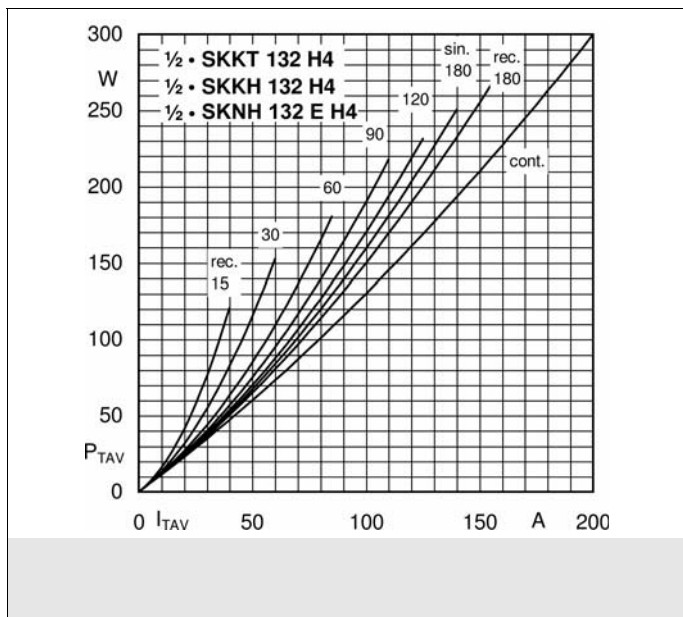


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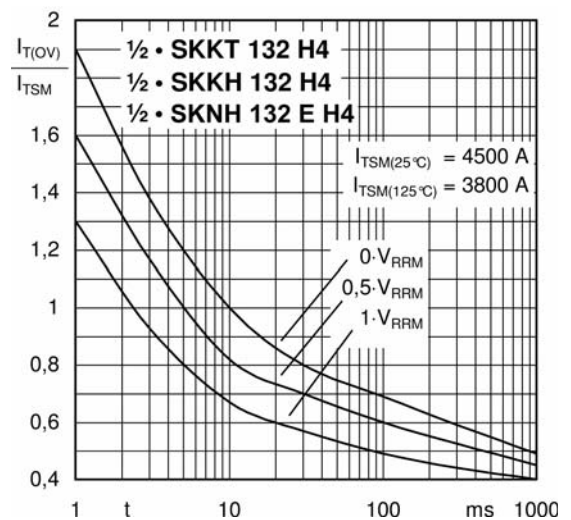
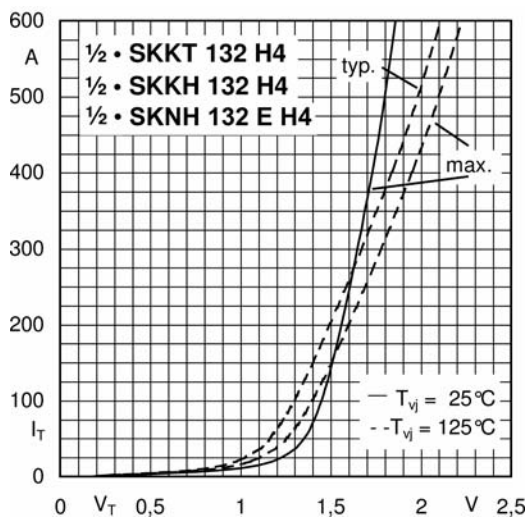
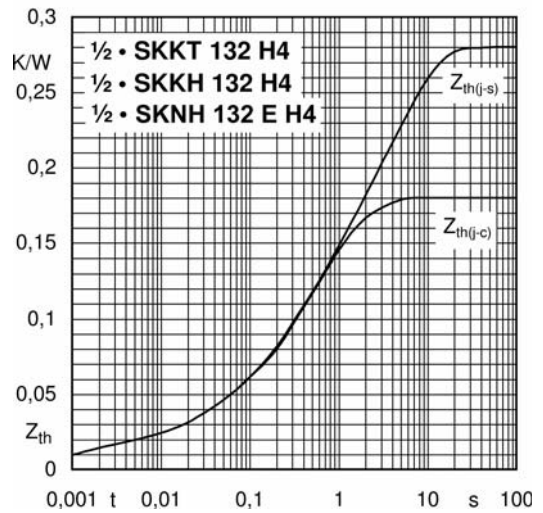
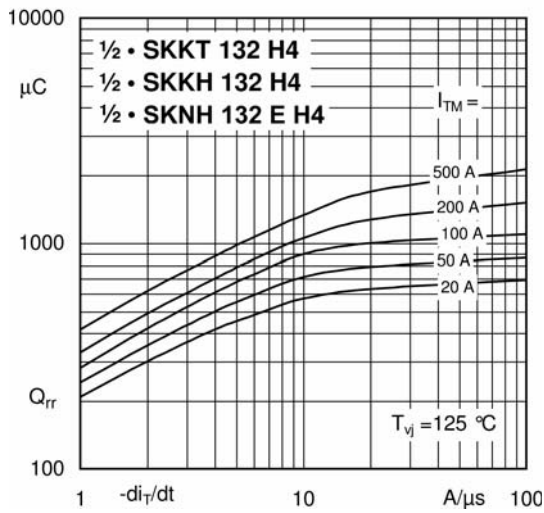
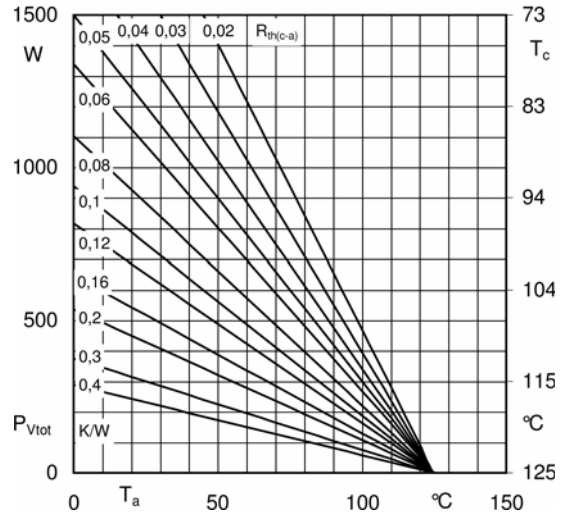
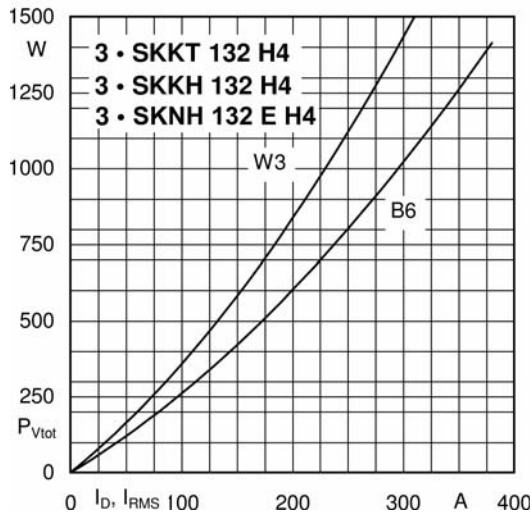
Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>Chip</b>				
$I_{T(AV)}$	sinus 180°	$T_c = 85\text{ °C}$	128	A
		$T_c = 100\text{ °C}$	86	A
$I_{TSM}$	10 ms	$T_j = 25\text{ °C}$	4700	A
		$T_j = 130\text{ °C}$	3800	A
$i^2t$	10 ms	$T_j = 25\text{ °C}$	110450	A <sup>2</sup> s
		$T_j = 130\text{ °C}$	72200	A <sup>2</sup> s
$V_{RSM}$			1800	V
$V_{RRM}$			1800	V
$V_{DRM}$			1800	V
$(di/dt)_{cr}$	$T_j = 125\text{ °C}$		200	A/μs
$(dv/dt)_{cr}$	$T_j = 125\text{ °C}$		1000	V/μs
$T_j$			-40 ... 125	°C
<b>Module</b>				
$T_{stg}$			-40 ... 125	°C
$V_{isol}$	a.c.; 50 Hz; r.m.s.	1 min	4000	V
		1 s	4800	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Chip</b>						
$V_T$	$T_j = 25\text{ °C}, I_T = 500\text{ A}$				1.8	V
$V_{T(TO)}$	$T_j = 125\text{ °C}$				1.1	V
$r_T$	$T_j = 125\text{ °C}$				2.00	mΩ
$I_{DD}; I_{RD}$	$T_j = 125\text{ °C}, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$				40	mA
$t_{gd}$	$T_j = 25\text{ °C}, I_G = 1\text{ A}, di_G/dt = 1\text{ A}/\mu\text{s}$			1		μs
$t_{gr}$	$V_D = 0.67 * V_{DRM}$			2		μs
$t_q$	$T_j = 125\text{ °C}$		50	150	150	μs
$I_H$	$T_j = 25\text{ °C}$			150	400	mA
$I_L$	$T_j = 25\text{ °C}, R_G = 33\text{ }\Omega$			300	1000	mA
$V_{GT}$	$T_j = 25\text{ °C}, \text{d.c.}$		2			V
$I_{GT}$	$T_j = 25\text{ °C}, \text{d.c.}$		150			mA
$V_{GD}$	$T_j = 125\text{ °C}, \text{d.c.}$				0.25	V
$I_{GD}$	$T_j = 115\text{ °C}, \text{d.c.}$				10	mA
$R_{th(j-c)}$	continuous DC	per chip			0.18	K/W
		per module			0.09	K/W
$R_{th(j-c)}$	sin. 180°	per chip			0.19	K/W
		per module			0.095	K/W
$R_{th(j-c)}$	rec. 120°	per chip			0.21	K/W
		per module			0.105	K/W
<b>Module</b>						
$R_{th(c-s)}$	chip			0.1		K/W
	module				0.05	K/W
$M_s$	to heatsink M5		4.25		5.75	Nm
$M_t$	to heatsink M6		4.25		5.75	Nm
$a$					5 * 9,81	m/s <sup>2</sup>
$w$				165		g

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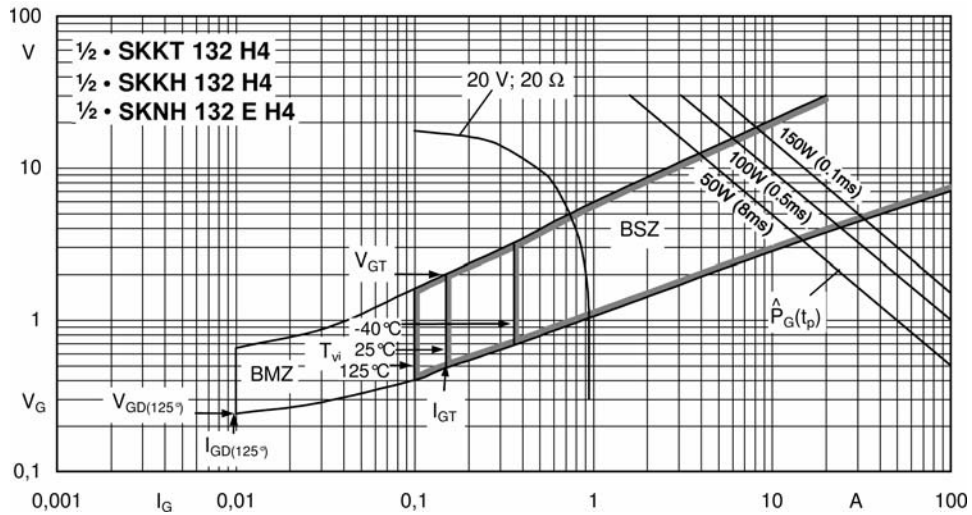
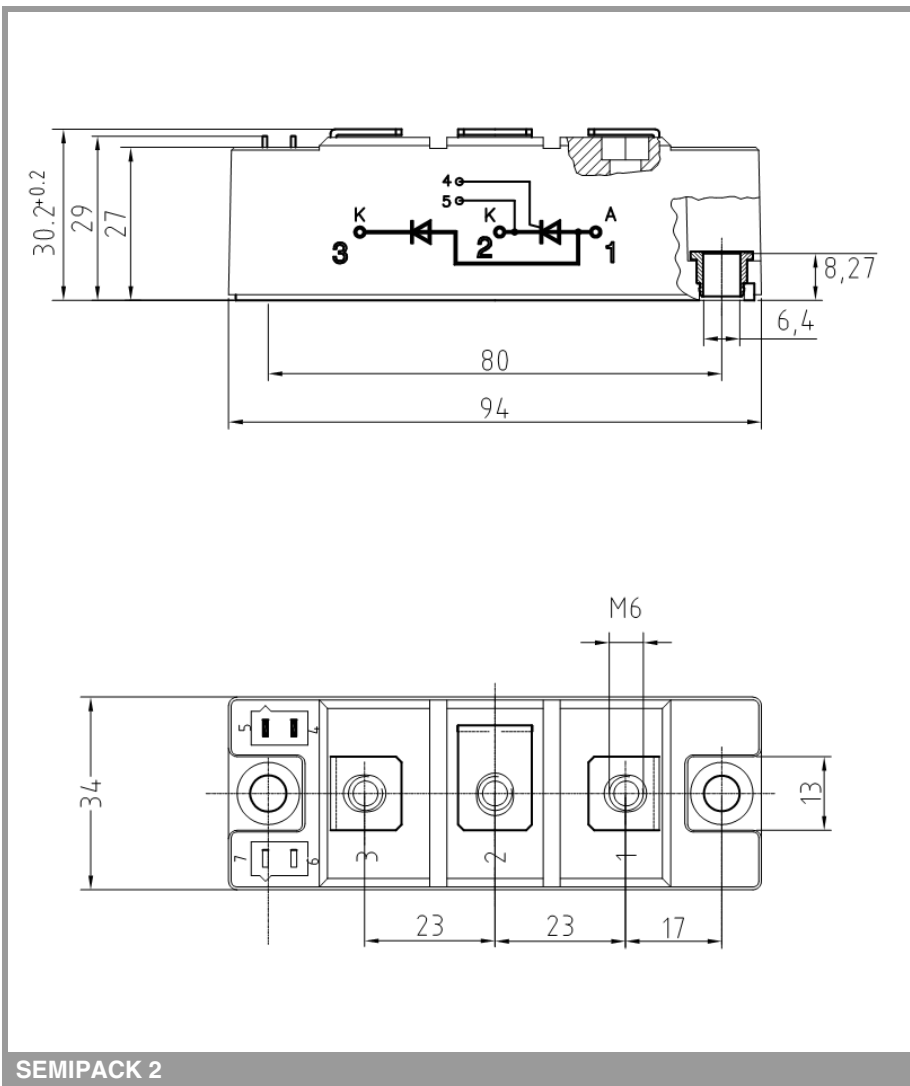


Fig. 9: Gate trigger characteristics



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.